

### Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

#### **Listing of Claims:**

Claims 1-9 (Canceled)

Claim 10 (Currently Amended): A method of depositing a wiring thin film over a semiconductor substrate, the method comprising:

providing a Al<sub>3</sub>Ti target;

providing a substrate;

forming a Ti layer over said substrate;

sputter depositing an Al<sub>3</sub>Ti layer on said Ti layer using said Al<sub>3</sub>Ti target;

depositing an Al layer onto said Al<sub>3</sub>Ti layer using an Al-Si-Cu target; and[[],]] after the sputter depositing[[],]]

annealing said substrate at a temperature of at least 400°C after said depositing  
an Al layer and without cooling said substrate, to promote absorption of Si from said Al  
layer into said Al<sub>3</sub>Ti layer.

Claim 11 (Canceled)

Claim 12 (Previously Presented): A method as recited in claim 10, further comprising pattern-etching said Al layer thereby forming a wiring pattern.

Claim 13 (Currently Amended): A method as recited in claim 10, ~~wherein the method further comprises comprising~~ forming an insulating layer between said substrate and said Al<sub>3</sub>Ti layer.

Claim 14 (Currently Amended): A method of forming a wiring film, the method comprising:

providing a substrate;  
depositing a Ti layer over said substrate;  
depositing an Al-Si-Cu Al layer on said Ti layer using an Al-Si-Cu target;  
~~pattern etching an Al layer, which forms beneath said Al-Si-Cu layer; and after the depositing of the Al-Si-Cu layer[.]~~  
annealing the substrate at a temperature of at least 400°C after said depositing an Al layer and without cooling the substrate, to form an Al<sub>3</sub>Ti layer on said Ti layer and to promote absorption of Si from said Al layer into said Al<sub>3</sub>Ti layer; and  
pattern etching said Al layer after said annealing.

Claims 15-16 (Canceled)

Claim 17 (Currently Amended): A method of forming a wiring film, the method comprising:

providing a substrate;

depositing a Ti layer over the substrate;

depositing an Al<sub>3</sub>Ti layer [[over]] on said substrate Ti layer using an Al<sub>3</sub>Ti target;

depositing an Al layer on said Al<sub>3</sub>Ti layer using an Al<sub>3</sub>Ti target;

~~pattern etching said Al layer; and after the depositing of the Al layer[[,]]~~

annealing the substrate at a temperature of at least 400°C after said depositing  
an Al layer and without cooling the substrate, to promote absorption of Si from said Al  
layer into said Al<sub>3</sub>Ti layer; and

pattern etching said Al layer after said annealing.

Claim 18 (Previously Presented): A method as recited in claim 17, wherein said Al layer is deposited at a temperature of at least 400°C.

Claim 19 (Cancelled)

Claim 20 (Previously Presented): A method as recited in claim 17, wherein said Al<sub>3</sub>Ti layer is deposited at a temperature of at least 400°C.

Claim 21 (New): A method as recited in claim 10, further comprising depositing a TiN film on said Al layer.

Claim 22 (New): A method as recited in claim 14, further comprising forming an insulating layer between said substrate and said Ti film.

Claim 23 (New): A method as recited in claim 14, further comprising depositing a TiN film on said Al layer.

Claim 24 (New): A method as recited in claim 17, further comprising forming an insulating layer between said substrate and said Al<sub>3</sub>Ti layer.

Claim 25 (New): A method as recited in claim 17, further comprising depositing a TiN film on said Al layer.